

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	623590	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:43
L2	239119	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:44
L3	16737	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press\$3 near9 (oxide or dielectric insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:47
L4	381	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press\$3 near9 (oxide or dielectric insulat\$4)) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:48
L5	52	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press\$3 near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:45
L6	27	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press\$3 near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply) and (support or frame)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:50

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L7	11	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press\$3 near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply) and (support or frame) and (plating near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:12
L8	3	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (b near stage) and (power near supply) and (support or frame) and (plating near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:13
L9	1982	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14
L10	937	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14
L11	86	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:15
L12	81	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage) and ((heat\$4 or thermal) near9 (oxide or dielectric or insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:21

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L13	3	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage) and ((heat\$4 or thermal) near9 (oxide or dielectric or insulat\$4)) and (power near supply)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:21
S1	0	("JP2001-537286") or ("JP2001-68850") or ("JP7-111375") or ("JP6-350258") or ("JP10-022636") or ("JP2002-137328") or ("JP2002-134881") or ("JP2002-076578").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/26 09:27
S2	37	"5600103"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S3	172	"power supply film"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S4	1	"power supply film" and insulat\$4 and conduct\$4 and "b-stage"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36
S5	4	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36
S6	3	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4 and curing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37

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S7	4	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4 and cur\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37
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